

NCE Automotive N-Channel Super Trench Power MOSFET

Description

The NCEAP6090AGU uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(on)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

- Automotive application
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

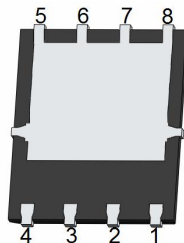
General Features

- $V_{DS} = 60V, I_D = 130A$
- $R_{DS(on)} = 2.8m\Omega$ (typical) @ $V_{GS} = 10V$
- $R_{DS(on)} = 3.5m\Omega$ (typical) @ $V_{GS} = 4.5V$
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- 100% UIS tested
- 100% ΔV_{ds} tested
- Pb-free lead plating
- **AEC-Q101 qualified**

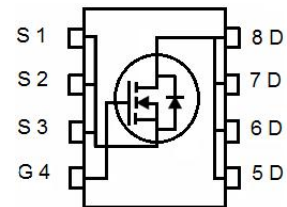
DFN 5X6



Top View



Bottom View



Schematic Diagram

Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|--------------|----------------|-----------|------------|----------|
| AP6090AGU | NCEAP6090AGU | DFN5X6-8L | - | - | - |

Absolute Maximum Ratings ($T_c = 25^\circ C$ unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|---|--------------------|------------|---------------|
| Drain-Source Voltage | V_{DS} | 60 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Drain Current-Continuous | I_D | 130 | A |
| Drain Current-Continuous ($T_c = 100^\circ C$) | $I_D(100^\circ C)$ | 92 | A |
| Pulsed Drain Current | I_{DM} | 520 | A |
| Maximum Power Dissipation | P_D | 120 | W |
| Derating factor | | 0.8 | W/ $^\circ C$ |
| Single pulse avalanche energy ^(Note 1) | E_{AS} | 500 | mJ |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 To 175 | $^\circ C$ |

Thermal Characteristic

| | | | |
|--------------------------------------|-----------------|------|--------------|
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 1.25 | $^\circ C/W$ |
|--------------------------------------|-----------------|------|--------------|

Electrical Characteristics (T_c=25°C unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---|---------------------|---|-----|------|------|------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V, I _D =250μA | 60 | | - | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =60V, V _{GS} =0V | - | - | 1 | μA |
| Gate-Body Leakage Current | I _{GSS} | V _{GS} =±20V, V _{DS} =0V | - | - | ±100 | nA |
| On Characteristics | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} , I _D =250μA | 1.0 | 1.7 | 2.2 | V |
| Drain-Source On-State Resistance | R _{DS(on)} | V _{GS} =10V, I _D =20A | - | 2.8 | 3.5 | mΩ |
| | | V _{GS} =4.5V, I _D =20A | - | 3.5 | 4.5 | mΩ |
| Forward Transconductance | g _{FS} | V _{DS} =10V, I _D =20A | 40 | - | - | S |
| Dynamic Characteristics | | | | | | |
| Input Capacitance | C _{iss} | V _{DS} =30V, V _{GS} =0V, F=1.0MHz | - | 4000 | - | PF |
| Output Capacitance | C _{oss} | | - | 680 | - | PF |
| Reverse Transfer Capacitance | C _{rss} | | - | 23 | - | PF |
| Switching Characteristics (Note 2) | | | | | | |
| Turn-on Delay Time | t _{d(on)} | V _{DD} =30V, I _D =20A V _{GS} =10V, R _G =4.7Ω | - | 11 | - | nS |
| Turn-on Rise Time | t _r | | - | 5 | - | nS |
| Turn-Off Delay Time | t _{d(off)} | | - | 56 | - | nS |
| Turn-Off Fall Time | t _f | | - | 12 | - | nS |
| Total Gate Charge | Q _g | V _{DS} =30V, I _D =20A, V _{GS} =10V | - | 67 | | nC |
| Gate-Source Charge | Q _{gs} | | - | 12 | | nC |
| Gate-Drain Charge | Q _{gd} | | - | 8.5 | | nC |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage | V _{SD} | V _{GS} =0V, I _S =20A | - | | 1.2 | V |
| Diode Forward Current | I _S | | - | - | 130 | A |
| Reverse Recovery Time | t _{rr} | T _J = 25°C, I _F = I _S di/dt = 100A/μs | - | 48 | | nS |
| Reverse Recovery Charge | Q _{rr} | | - | 60 | | nC |

Notes:

1. EAS condition : T_j=25°C, V_{DD}=30V, V_G=10V, L=0.5mH, R_G=25Ω
2. Guaranteed by design, not subject to production
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=175° C. The SOA curve provides a single pulse rating.

Typical Electrical and Thermal Characteristics

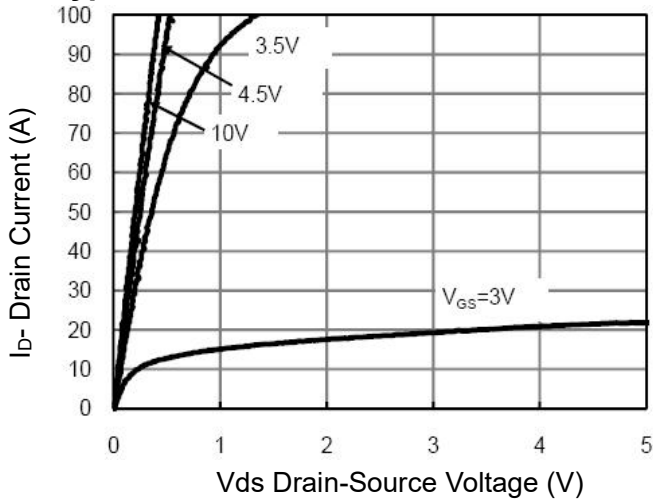


Figure 1 Output Characteristics

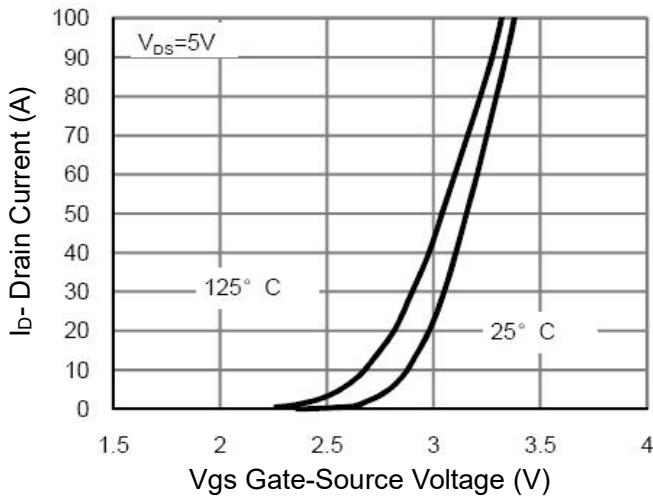


Figure 2 Transfer Characteristics

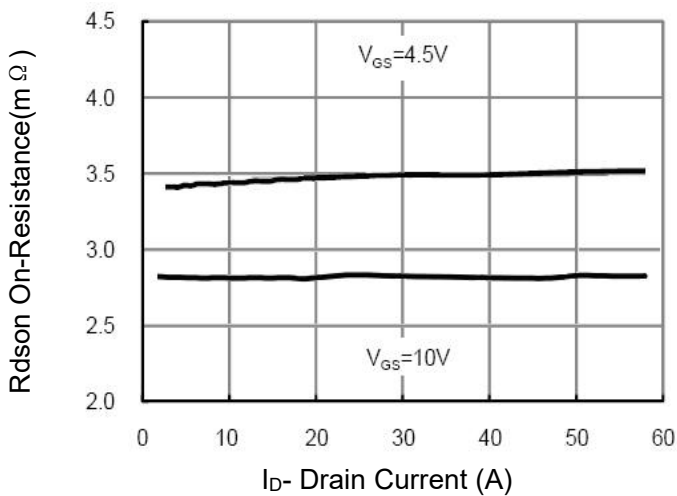


Figure 3 Rdson- Drain Current

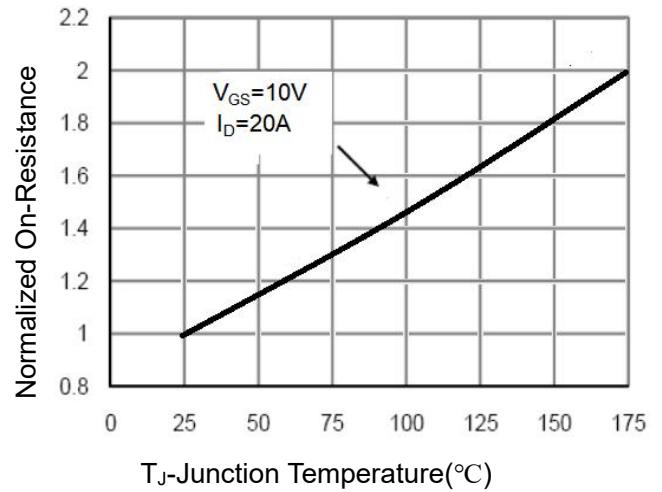


Figure 4 Rdson-Junction Temperature

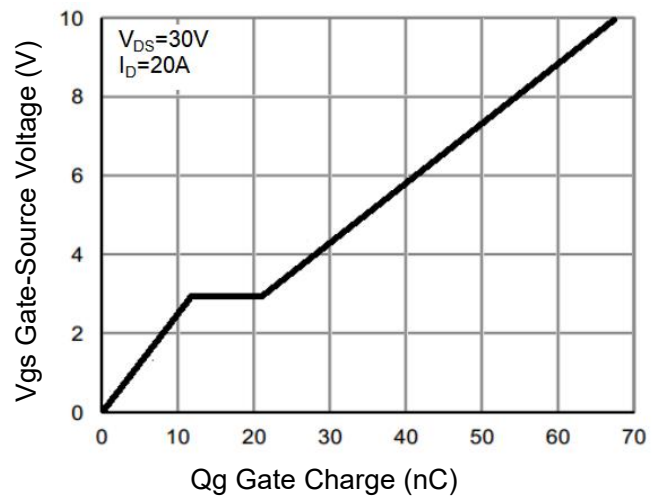


Figure 5 Gate Charge

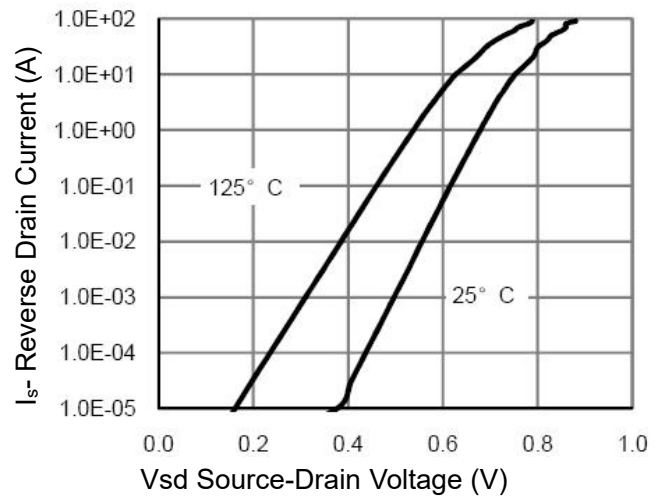


Figure 6 Source- Drain Diode Forward

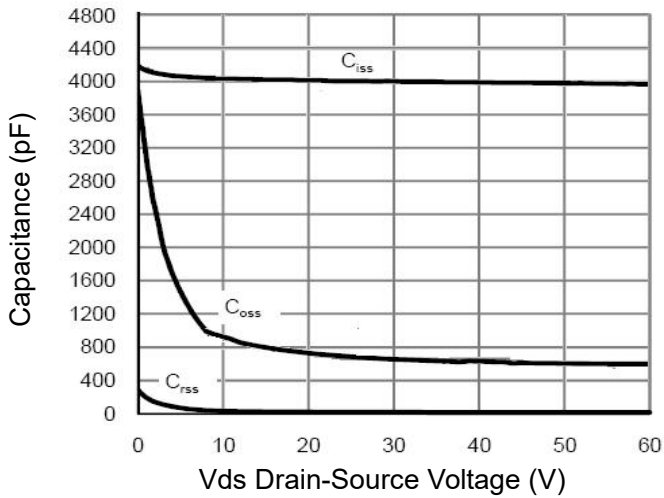


Figure 7 Capacitance vs Vds

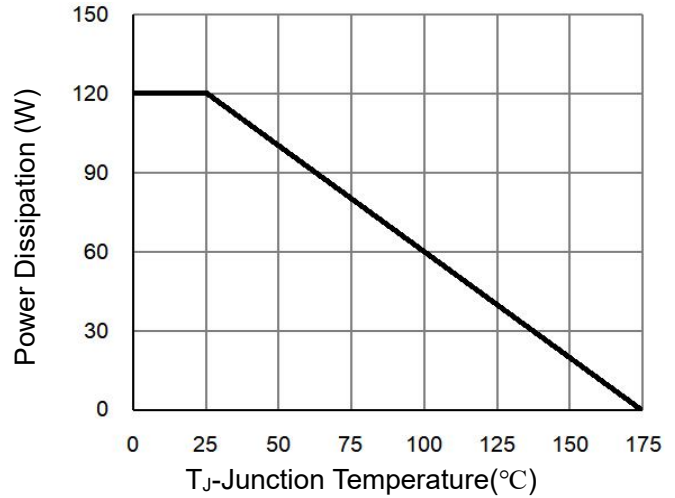


Figure 9 Power De-rating

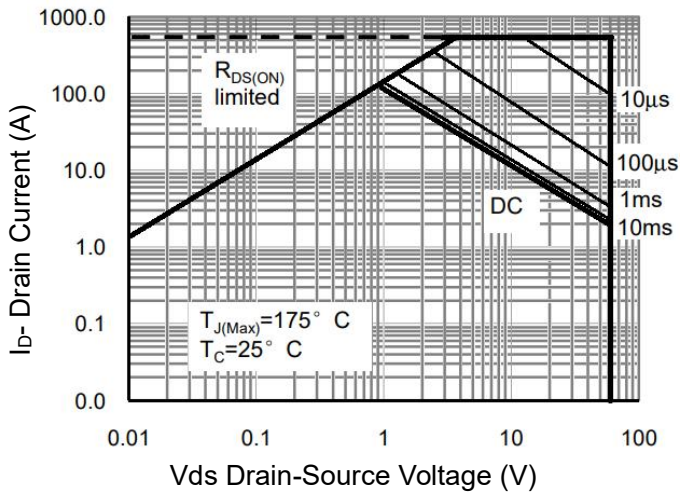


Figure 8 Safe Operation Area (Note3)

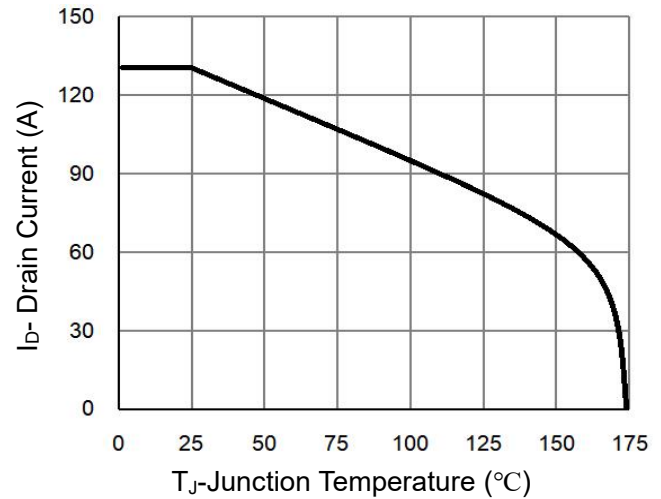


Figure 10 Current De-rating

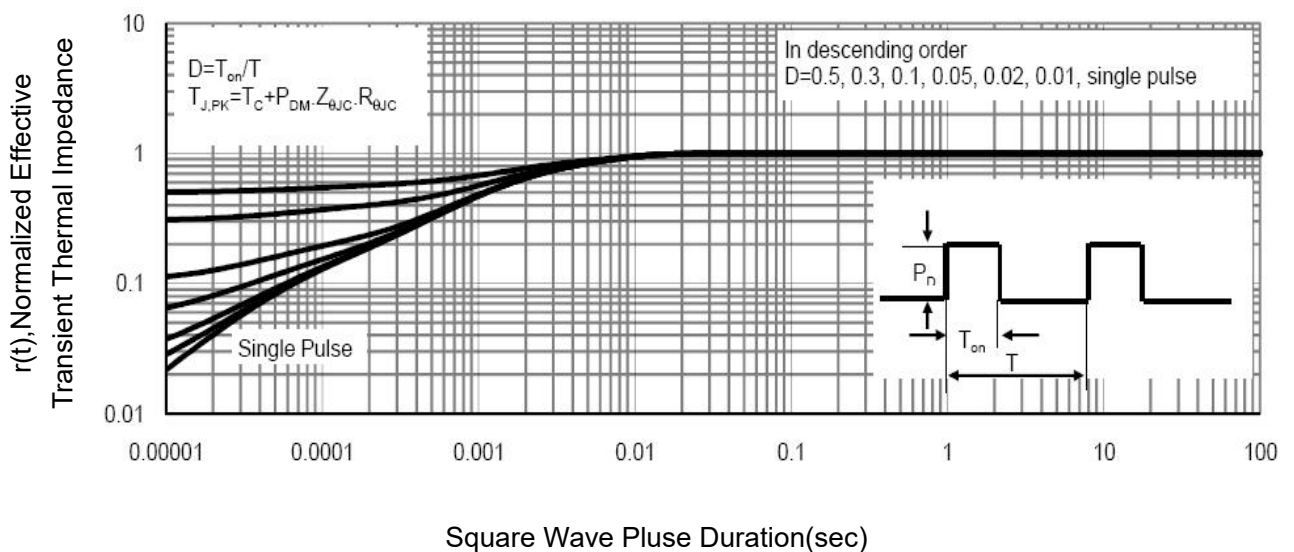
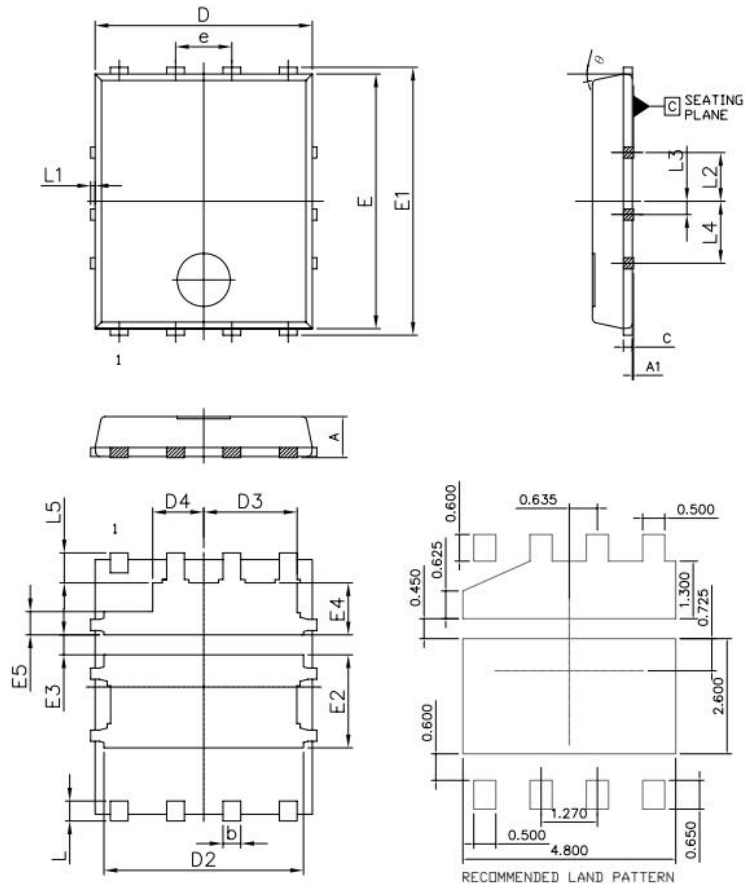


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN5X6-8L Package Information



| DIM | MILLIMETERS | | |
|-----|-------------|-------|-------|
| | MIN | NOM | MAX |
| A | 0.85 | 0.90 | 1.00 |
| A1 | 0.00 | / | 0.05 |
| b | 0.35 | 0.40 | 0.48 |
| c | 0.15 | 0.20 | 0.28 |
| D | 4.80 | 4.90 | 5.00 |
| D2 | 4.30 | 4.50 | 4.70 |
| D3 | 1.955 | 2.105 | 2.255 |
| D4 | 1.000 | 1.150 | 1.300 |
| E | 5.65 | 5.75 | 5.85 |
| E1 | 5.90 | 6.05 | 6.20 |
| E2 | 1.95 | 2.10 | 2.25 |
| E3 | 0.30 | 0.45 | 0.60 |
| E4 | 1.025 | 1.175 | 1.325 |
| E5 | 0.375 | 0.525 | 0.675 |
| e | / | 1.27 | / |
| L | 0.35 | 0.45 | 0.55 |
| L1 | 0 | / | 0.15 |
| L2 | 1.00 | 1.10 | 1.20 |
| L3 | 0.20 | 0.30 | 0.40 |
| L4 | 1.30 | 1.40 | 1.50 |
| L5 | 0.575 | 0.675 | 0.775 |
| θ | 0° | 12° | 14° |

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